Silicon P Channel Power MOS FET High Speed Power Switching

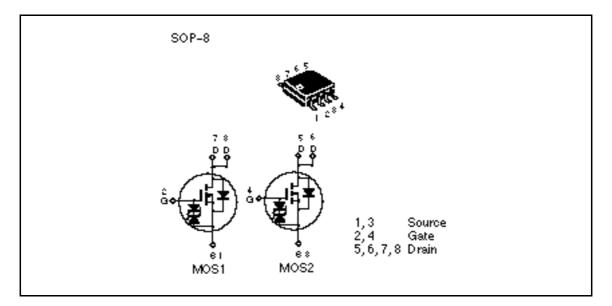


ADE-208-663C (Z) 4th. Edition February 1999

#### Features

- For Automotive Application ( at Type Code "J")
- Low on-resistance
- Capable of 4 V gate drive
- High density mounting

#### Outline





## **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

| Item                                   |           | Symbol                           | Ratings     | Unit |
|--|-----------|----------------------------------|-------------|------|
| Drain to source voltage                |           | V <sub>DSS</sub>                 | -60         | V    |
| Gate to source voltage                 |           | V <sub>GSS</sub>                 | ±20         | V    |
| Drain current                          |           | I <sub>D</sub>                   | -3.5        | А    |
| Drain peak current                     |           | Note1<br>D(pulse)                | -28         | A    |
| Body-drain diode reverse drain current |           | I <sub>DR</sub>                  | -3.5        | A    |
| Avalanche current                      | HAT1038R  | I Note4                          | _           | _    |
|  | HAT1038RJ | -                                | -3.5        | A    |
| Avalanche energy                       | HAT1038R  | E <sub>AR</sub> <sup>Note4</sup> | _           | _    |
|  | HAT1038RJ | -                                | 1.05        | mJ   |
| Channel dissipation                    |           | Pch Note2                        | 2           | W    |
| Channel dissipation                    |           | Pch Note3                        | 3           | W    |
| Channel temperature                    |           | Tch                              | 150         | °C   |
| Storage temperature                    |           | Tstg                             | -55 to +150 | °C   |

Note: 1. PW 10 $\mu$ s, duty cycle 1 %

2. 1 Drive operation ; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW  $\,$  10s  $\,$ 

3. 2 Drive operation ; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW 10s

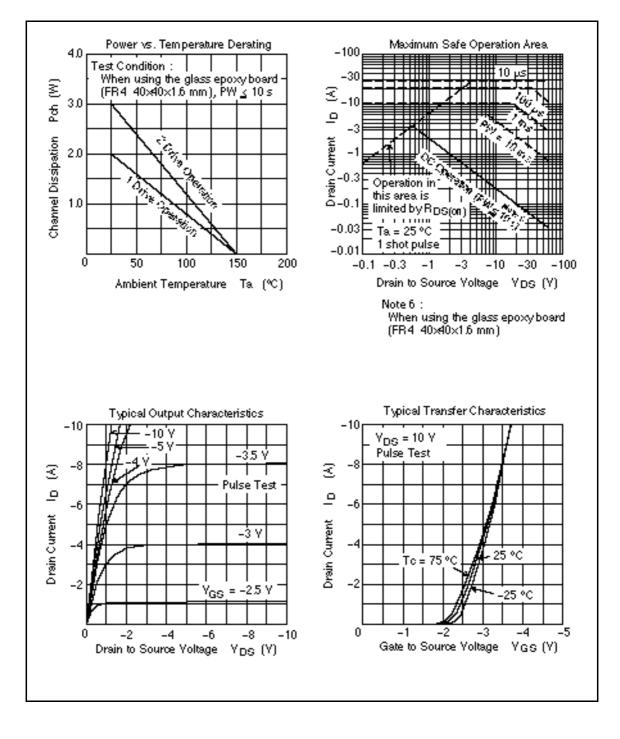
4. Value at Tch=25°C, Rg 50

| Item                                   |           | Symbol               | Min  | Тур   | Max   | Unit | Test Conditions  |
|--|-----------|----------------------|------|-------|-------|------|--|
| Drain to source breakdown voltage      |           | $V_{(BR)DSS}$        | -60  | —     | —     | V    | $I_{\rm D} = -10 {\rm mA}, V_{\rm GS} = 0$   |
| Gate to source breakdown voltage       |           | $V_{(BR)GSS}$        | ±20  |       | —     | V    | $I_{g} = \pm 100 \mu A, V_{DS} = 0$  |
| Gate to source leak current            |           | I <sub>GSS</sub>     |      |       | ±10   | μA   | $V_{GS} = \pm 16V, V_{DS} = 0$   |
| Zero gate voltage                      | HAT1038R  | I <sub>DSS</sub>     |      |       | -1    | μA   | $V_{\rm DS} = -60V, V_{\rm GS} = 0$  |
| drain current                          | HAT1038RJ | I <sub>DSS</sub>     |      |       | -0.1  | μA   | _  |
| Zero gate voltage                      | HAT1038R  | I <sub>DSS</sub>     |      |       | _     | μA   | $V_{\rm DS} = -48V, V_{\rm GS} = 0$  |
| drain current                          | HAT1038RJ | I <sub>DSS</sub>     |      |       | -10   | μA   | Ta=125°C   |
| Gate to source cutoff voltage          |           | $V_{\text{GS(off)}}$ | -1.2 |       | -2.2  | V    | $V_{DS} = -10V, I_{D} = -1mA$  |
| Static drain to source on state        |           | $R_{DS(on)}$         |      | 0.12  | 0.15  |      | $I_{\rm D} = -2A, V_{\rm GS} = -10V^{\rm Note5}$   |
| resistance                             |           | R <sub>DS(on)</sub>  |      | 0.16  | 0.23  |      | $I_{\rm D} = -2A, V_{\rm GS} = -4V^{\rm Note5}$  |
| Forward transfer admittance            |           | y <sub>fs</sub>      | 3    | 4.5   | _     | S    | $I_{\rm D} = -2A, V_{\rm DS} = -10V^{\rm Note5}$   |
| Input capacitance                      |           | Ciss                 |      | 600   | _     | pF   | $V_{DS} = -10V$  |
| Output capacitance                     |           | Coss                 |      | 290   | _     | pF   | $V_{GS} = 0$   |
| Reverse transfer capacitance           |           | Crss                 |      | 75    | _     | pF   | f = 1MHz   |
| Turn-on delay time                     |           | t <sub>d(on)</sub>   |      | 11    | _     | ns   | $V_{GS} = -10V, I_{D} = -2A$   |
| Rise time                              |           | t <sub>r</sub>       |      | 30    | _     | ns   | V <sub>DD</sub> -30V   |
| Turn-off delay time                    |           | $t_{d(off)}$         | _    | 100   | _     | ns   | _  |
| Fall time                              |           | t <sub>f</sub>       | _    | 55    | _     | ns   | _  |
| Body-drain diode forward voltage       |           | $V_{\text{DF}}$      | _    | -0.98 | -1.28 | V    | $IF = -3.5A, V_{GS} = 0^{Note5}$   |
| Body–drain diode reverse recovery time |           | t <sub>rr</sub>      |      | 70    | —     | ns   | $\label{eq:IF} \begin{array}{l} IF=-3.5A,V_{_{\mathrm{GS}}}=0\\ diF/dt=\!\!50A/\!\mus \end{array}$ |

## **Electrical Characteristics** (Ta = $25^{\circ}$ C)

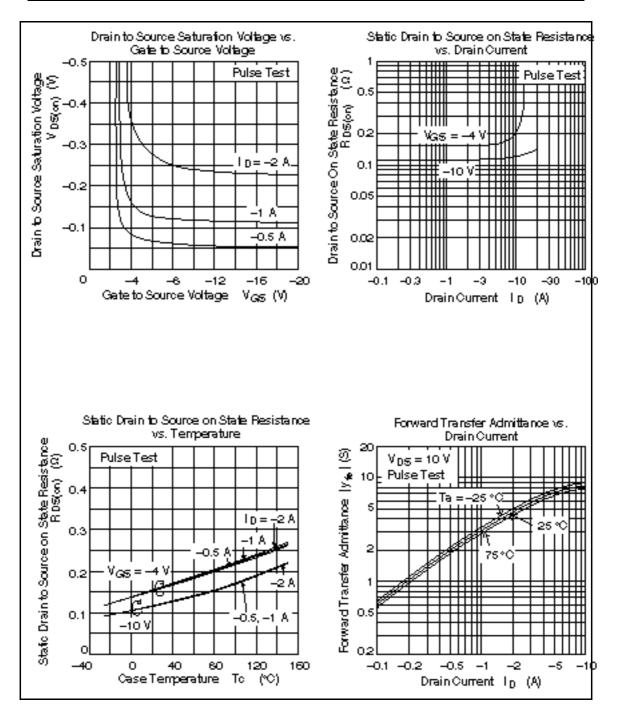
Note: 5. Pulse test

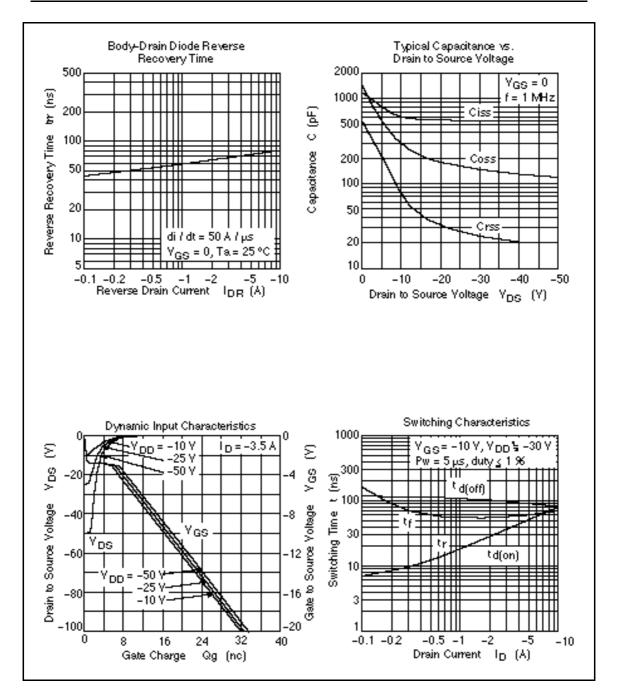
#### **Main Characteristics**

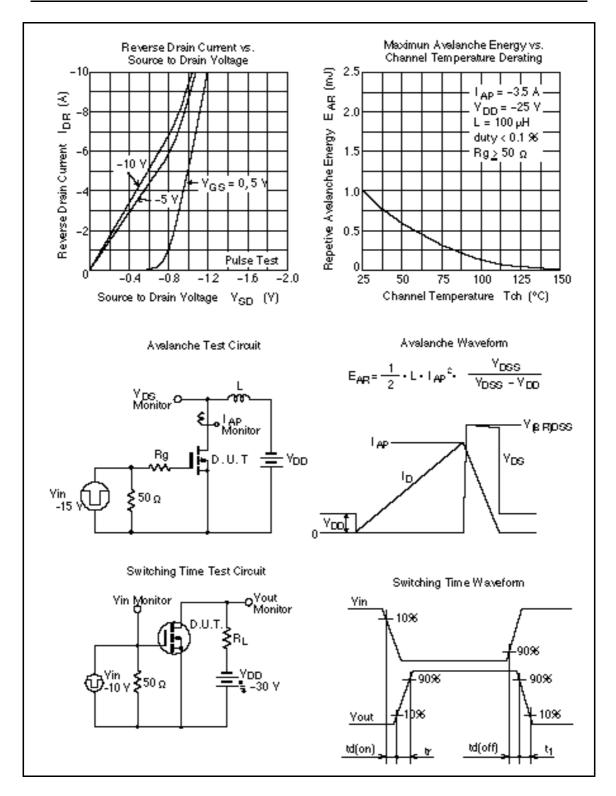


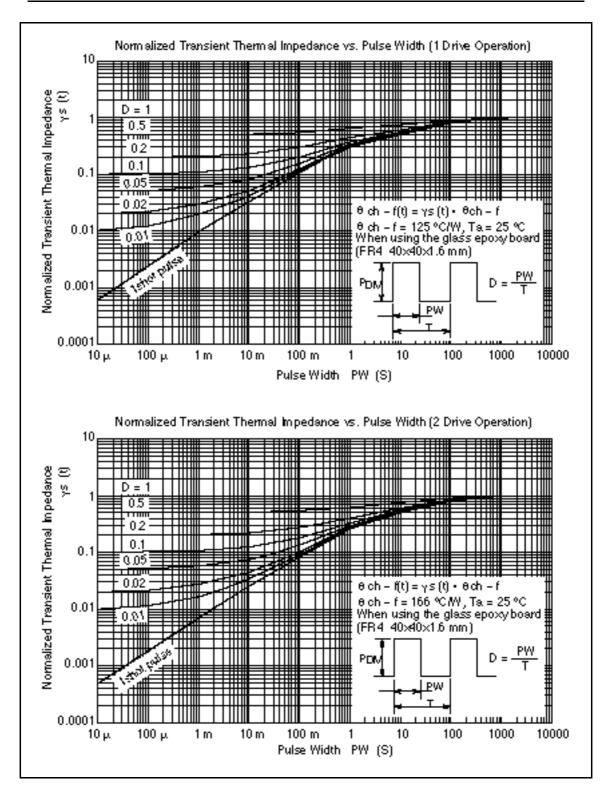
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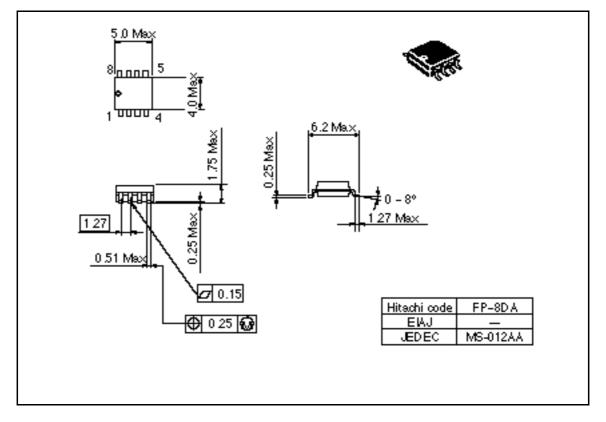






## **Package Dimensions**

Unit: mm



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Hitachi, Ltd. Semiconductor & IC Div

NipponBidt, 24-2 Ohle-madri, Chiyoda-ku, Tokyo 100.0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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Hischill 🖮 Ltd. Misain Ann 183 Taipei Brund Office 37, Hung Kuo Building, Na 167, Tun-Hwa North Road, Taipei (105) Tal: 28866 (2) 2718-8586 Fax: 28866 (2) 2718-8180 Hinachi Azin (Hong Kong) Ltd. Group III (Bectronic Componente) 7/F., North Tower, World Finance Centre, Herbour Oby, Canton Road, Teim She Teui, Kandroo Marce Kan Hensbour Oby, Oensbon Koes Kowloon, Hong Kong Tel:⊲825⊳(2) 735 92 18 Fex:⊲852⊳(2) 730 0281 Tele:40815 НПЕСНХ

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